



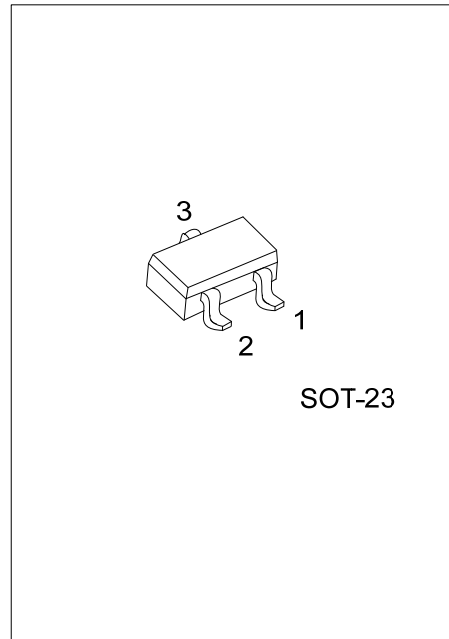
MMBT5551

NPN SILICON TRANSISTOR

HIGH VOLTAGE SWITCHING TRANSISTOR

■ FEATURES

- * High Collector-Emitter Voltage: $V_{CE0}=160V$
- * High current gain



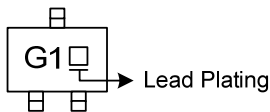
Lead-free: MMBT5551L
 Halogen-free: MMBT5551G

■ ORDERING INFORMATION

Ordering Number			Package	Pin Assignment			Packing
Normal	Lead Free Plating	Halogen-Free		1	2	3	
MMBT5551-x-AE3-R	MMBT5551L-x-AE3-R	MMBT5551G-x-AE3-R	SOT-23	E	B	C	Tape Reel

<p>MMBT5551L-x-AE3-R</p>	<p>(1) Packing Type (2) Package Type (3) Rank (4) Lead Plating</p>	<p>(1) R: Tape Reel (2) AE3: SOT-23 (3) x: refer to Classification of h_{FE} (4) G: Halogen Free, L: Lead Free Plating, Blank: Pb/Sn</p>
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■ MARKING



MMBT5551

NPN SILICON TRANSISTOR

■ ABSOLUTE MAXIMUM RATINGS (Ta = 25°C)

PARAMETER	SYMBOL	RATINGS	UNIT
Collector -Base Voltage	V _{CBO}	180	V
Collector -Emitter Voltage	V _{CEO}	160	V
Emitter -Base Voltage	V _{EBO}	6	V
DC Collector Current	I _C	600	mA
Power Dissipation	P _D	350	mW
Junction Temperature	T _J	+150	°C
Storage Temperature	T _{STG}	-40 ~ +150	°C

Note Absolute maximum ratings are those values beyond which the device could be permanently damaged. Absolute maximum ratings are stress ratings only and functional device operation is not implied.

■ ELECTRICAL CHARACTERISTICS (Ta= 25°C, unless otherwise specified)

PARAMETER	SYMBOL	TEST CONDITIONS	MIN	TYP	MAX	UNIT
Collector-Base Breakdown Voltage	V _{CBO}	I _C =100μA, I _E =0	180			V
Collector-Emitter Breakdown Voltage	V _{CEO}	I _C =1mA, I _B =0	160			V
Emitter-Base Breakdown Voltage	V _{EBO}	I _E =10μA, I _C =0	6			V
Collector Cut-off Current	I _{CBO}	V _{CB} =120V, I _E =0			50	nA
Emitter Cut-off Current	I _{EBO}	V _{BE} =4V, I _C =0			50	nA
DC Current Gain(note)	h _{FE}	V _{CE} =5V, I _C =1mA V _{CE} =5V, I _C =10mA V _{CE} =5V, I _C =50mA	80 80 80	160	400	
Collector-Emitter Saturation Voltage	V _{CE(SAT)}	I _C =10mA, I _B =1mA I _C =50mA, I _B =5mA			0.15 0.2	V
Base-Emitter Saturation Voltage	V _{BE(SAT)}	I _C =10mA, I _B =1mA I _C =50mA, I _B =5mA			1 1	V
Current Gain Bandwidth Product	f _T	V _{CE} =10V, I _C =10mA, f=100MHz	100		300	MHz
Output Capacitance	C _{ob}	V _{CB} =10V, I _E =0, f=1MHz			6.0	pF
Noise Figure	NF	I _C =0.25mA, V _{CE} =5V R _S =1kΩ, f=10Hz ~ 15.7kHz			8	dB

Note: Pulse test: PW<300μs, Duty Cycle<2%

■ CLASSIFICATION OF h_{FE}

RANK	A	B	C
RANGE	80-170	150-240	200-400



TYPICAL CHARACTERISTICS

Fig.1 Collector Output Capacitance

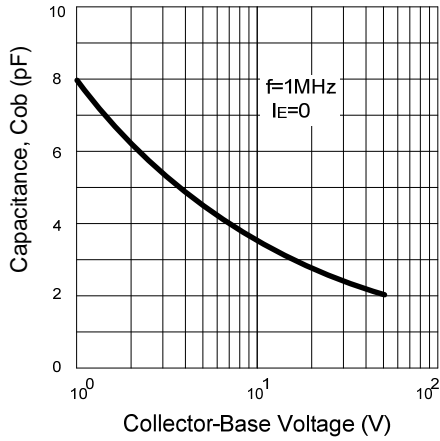


Fig.2 DC Current Gain

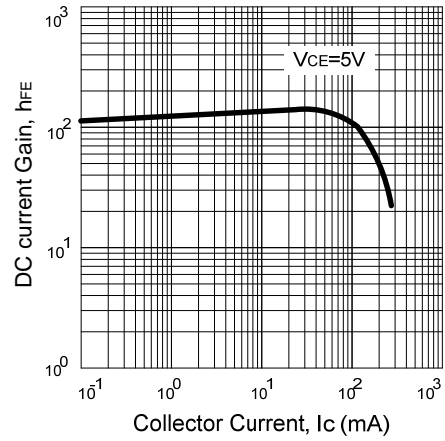


Fig.3 Base-Emitter on Voltage

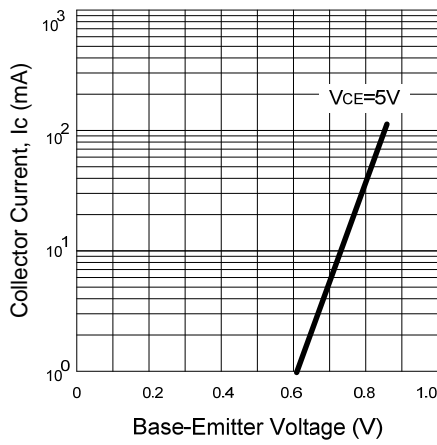


Fig.4 Saturation Voltage

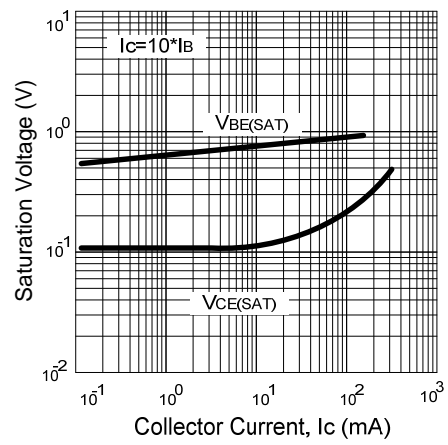
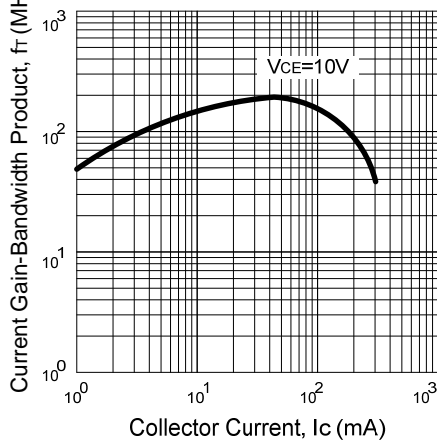


Fig.5 Current Gain-Bandwidth Product



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